

In the Specification:

Please replace the paragraph beginning at page 2, line 2 with the following rewritten paragraph:

A1
- This application is a divisional of application serial number 09/249,659, filed on February 12, 1999, now U.S. Patent No. 6,107,686, which is a divisional application of serial number 08/677,514, filed on July 10, 1996, now U.S. Patent No. 6,107,183, both of which are incorporated herein by reference. -

Please replace the paragraph beginning at page 3, line 9 with the following rewritten paragraph:

A2
- One way to decrease unneeded capacitance between metal lines in an integrated circuit is to decrease the dielectric constant of the material between them. Silicon dioxide, the material of choice for interlevel dielectrics, has a relatively high dielectric constant. Replacing silicon dioxide with a material having a lower dielectric constant would thus provide reduced capacitance. Useable materials having a low dielectric constant (e.g. less than about 3.6.) are generally much less stable than silicon dioxide and are thus unable to reliably protect the metal lines, and are unable to withstand further processing. -

Please replace the paragraph beginning at page 3, line 16 with the following rewritten paragraph:

Q3
One way to gain some of the benefits of low dielectric constant materials is shown in Figure 1. Figure 1 is a partial cross section of a partially formed integrated circuit device. A substrate or lower layer 12 has a first dielectric layer 14 comprised of a traditional dielectric material such as silicon dioxide. Lines of conductive material 16, typically metal, overlie first dielectric layer 14. A material with a dielectric constant lower than that of silicon dioxide 18 is located in between lines of conductive material 16. Lines of conductive material 16 together with low dielectric constant dielectric material 18 are covered by a second dielectric layer 21 comprised of a traditional dielectric material such as silicon dioxide. Second dielectric layer 21 together with first dielectric layer 14 isolate low dielectric constant dielectric material 18 from other portions of the integrated circuit. Second dielectric layer 21 allows further processing, including formation of contact holes for contacting lines of conductive material 16 such as contact hole 46, without exposing dielectric material 18 to processing agents.

Please replace the paragraph beginning at page 5, line 2 with the following rewritten paragraph:

Q4 In accordance with the present invention, an interlevel dielectric structure includes first and second dielectric layers between which are located lines of a conductive material with a dielectric material in spaces between the lines of conductive material, with the lower surface of the dielectric material extending lower than the lower surface of lines of conductive material adjacent thereto, and the upper surface of the dielectric material extending higher than the upper surface of lines of conductive material adjacent thereto, thus reducing fringe and total capacitance between the lines of conductive material. The dielectric material, which has a dielectric constant of less than about 3.6, does not extend directly above the upper surface of the lines of conductive material, allowing formation of subsequent contacts down to the lines of conductive material without exposing the dielectric material to further processing.